Dear Committee,

I enjoy editing scientific manuscripts and improve research papers, technical reports, and student thesis throughout my career. I detect awkwardness, re-work unclear expressions and sentences, and reduce usage of the passive voice to ensure clear, focused and concise presentation of all the required information. I improve an article abstract, suggest headlines, and provide support in answering the reviewer's comments. I strive to aid researchers to communicate findings or developments to a targeted audience. I edit in a broad subject area – physics, solid state physics, semiconductor physics, materials science, and electronic engineering. I fulfill technical requirements to process materials in Word and provide explanations and comments to clients. Also, I work with pdf and ppt documents.

Yours faithfully,

Yanina

Name	Yanina Fedorenko
Nationality	Belgian
Language	English, Dutch, Russian basic French and Finnish
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Education

Engineer-Physicist, Microelectronics and Electronic Materials, Saratov State University	**1993**
PhD in Physics and Mathematics, major in Physics of Semiconductors and Dielectrics (Solid State Physics), Saratov State University, Russia	**1998**

Work Experience

Postdoctoral Researcher, Aalto University	**2017**
Research Associate, the University of Liverpool	**2015**
Research Fellow, the University of Surrey	**2013-2014**
R&D Engineer, Photovoltech NV	**2008-2011**
Process Engineer, ASM Belgium	**2005-2007**
Postdoctoral Fellow, Katholieke Universiteit Leuven	**2003-2005**
Postdoctoral Researcher, Tampere University of Technology	**2001-2003**
Docent, Saratov State University	**2000-2001**
Assistant, Saratov State University	**1998-2000**
Visiting PhD Student, Helsinki University of Technology	**1996**
Doctoral Student, Saratov State University	**1993-1998**

Editorial subject areas

	1998-2000
	1993-2001
	1996-2001

- Physics
- Materials Science (Semiconductor Physics; Solid State Physics; Condensed Mater Physics; Chemical Engineering; Electrical Engineering)

Selected publications

1. Fedorenko Y. G., Major J. D., Pressman A., Phillips L. J., and Durose K., Modification of electron states in CdTe absorber due to a buffer layer in CdTe/CdS solar cells, J. Appl. Phys. **118**, 165705 (2015).
2. Fedorenko Y. G. Hughes M. A., Colaux J. L., Jeynes C., Gwilliam R. M., Homewood K. P., Yao J., Hewak D. W., Lee T.-H., Elliott S. R., Gholipour B., Curry R. J., Electrical properties of Bi-implanted amorphous chalcogenide films, Thin Solid Films **589**, 369 (2015).
3. Hughes, M. A., Fedorenko, Y., Gholipour, B., Yao, J., Lee, T.-H., Gwilliam, R. M., Homewood, K. P., Hinder, S., Hewak, D., Hinder S., Elliott, S. R., Curry, R. J., N-type chalcogenides by ion implantation, Nature Comm. **5**, 5346 (2014).
4. Hughes M.A., Fedorenko Y., Gwilliam R.M., Homewood K. P., Hinder S., Gholipour B., Hewak D. W., Lee T.-H., Elliott S. R., and Curry R. J., Ion-implantation-enhanced chalcogenide-glass resistiveswitching devices, Appl. Phys. Lett. **105**, 083506 (2014).

5. Fedorenko, Y., Swerts, J., Maes, J.W., Tois, E., Haukka, S., Wang, C.-G., Wilk, G., Delabie, A., De Gendt, S., Atomic layer deposition of hafnium silicate from $HfCl_4$, $SiCl_4$, and H_2O, Electrochem. Solid-State Lett. **10**, 149 (2007).
6. Fedorenko, Y.G., Truong, L., Afanas'ev, V.V., Stesmans, A., Zhang, Z., Campbell, S.A., Impact of nitrogen incorporation on interface states in (100)Si/HfO_2, J. Appl. Phys. **98**, 123703 (2005).
7. Afanas'ev, V.V., Fedorenko, Y.G., Stesmans, A., Interface traps and dangling-bond defects in (100)Ge/HfO_2, Appl. Phys. Lett. **87**, 032107 (2005).
8. Fedorenko, Y.G., Truong, L., Afanas'ev, V.V., Stesmans, A., Energy distribution of the (100)Si/HfO2 interface states, Appl. Phys. Lett. **84**, 4771 (2004).
9. Fedorenko, Y., Jouhti, T., Pavelescu, E.-M., Karirinne, S., Kontinnen, J., Pessa, M., Optimisation of growth temperature and post-growth annealing for GaInNAs/GaNAs/GaAs quantum-well structures emitting at 1.3 μm, Thin Solid Films **440**, 195 (2003).